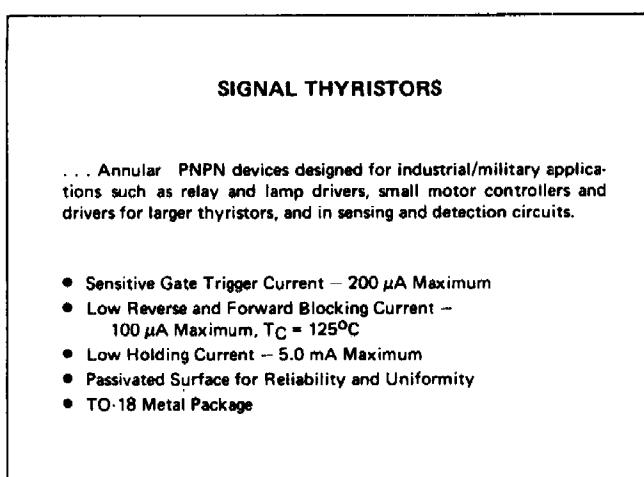
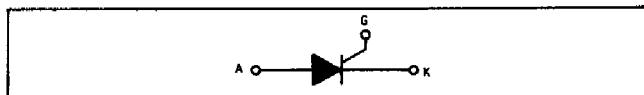


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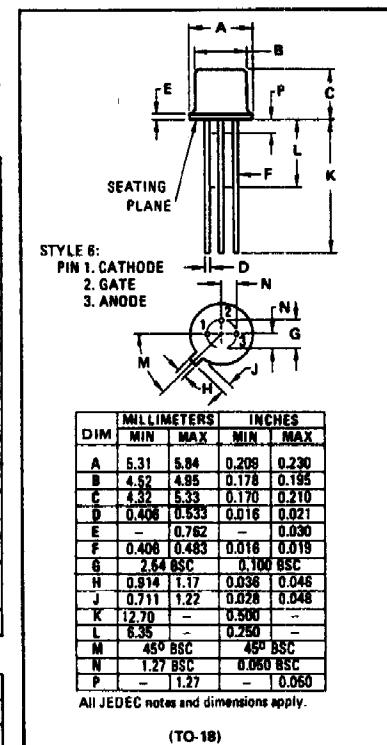
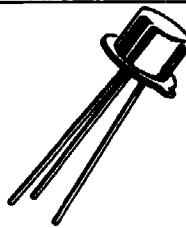
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MCR201 (SILICON) thru MCR206



SILICON CONTROLLED RECTIFIERS

0.5 AMPERE RMS
15 thru 200 VOLTS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Reverse Blocking Voltage	V_{RRM}		Volts
MCR201		15	
MCR202		30	
MCR203		60	
MCR204		100	
MCR205		150	
MCR206		200	
Forward Current RMS (See Figures 4 & 5) (All Conduction Angles)	$I^T(\text{RMS})$	0.5	Amp
Peak Forward Surge Current, $T_A = 25^\circ\text{C}$ (1/2 cycle, Sine Wave, 60 Hz)	I^{TSM}	6.0	Amp
Circuit Fusing Considerations, $T_A = 25^\circ\text{C}$ ($t = 1.0$ to 8.3 ms)	I^2t	0.15	A^2s
Peak Gate Power - Forward, $T_A = 25^\circ\text{C}$	P_{GM}	0.1	Watt
Average Gate Power - Forward, $T_A = 25^\circ\text{C}$	$P_{GF(AV)}$	0.01	Watt
Peak Gate Current - Forward, $T_A = 25^\circ\text{C}$ (300 μ s, 120 PPS)	I^{GFM}	1.0	Amp
Peak Gate Voltage - Reverse	V_{GRM}	4.0	Volts
Operating Junction Temperature Range @ Rated V_{RRM} and $V_{DRM(1)}$	T_J	-65 to +110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	150	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	θ_{JA}	400	$^\circ\text{C/W}$

(1) Higher Temperature Devices Available - Consult Factory.

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors



MCR201 thru MCR206 (continued)

ELECTRICAL CHARACTERISTICS ($R_{GK} = 1000$ Ohms)

Characteristic	Symbol	Min	Max	Unit
Peak Forward Blocking Voltage (Note 1)	V_{DRM}			Volts
MCR201		15	—	
MCR202		30	—	
MCR203		60	—	
MCR204		100	—	
MCR205		150	—	
MCR206		200	—	
Peak Forward Blocking Current (Rated V_{DRM} @ $T_C = 110^\circ\text{C}$)	I_{DRM}	—	100	μA
Peak Reverse Blocking Current (Rated V_{RRM} @ $T_C = 110^\circ\text{C}$)	I_{RRM}	—	1.5	μA
Forward "On" Voltage (Note 2) ($I_{TM} = 500$ mA peak @ $T_A = 25^\circ\text{C}$)	V_{TM}	—	1.7	Volts
Gate Trigger Current (Continuous dc) (Note 3) (Anode Voltage = 7.0 Vdc, $R_L = 100$ Ohms)	I_{GT}	—	200	μA
$T_C = 25^\circ\text{C}$		—	350	
$T_C = -65^\circ\text{C}$		—		
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 7.0 Vdc, $R_L = 100$ Ohms) (Anode Voltage = Rated V_{DRM})	V_{GT}	—	0.8	Volts
$T_C = 25^\circ\text{C}$		—	1.2	
$T_C = -65^\circ\text{C}$		0.1	—	
Holding Current (Anode Voltage = 7.0 Vdc, initiating current = 20 mA)	I_H	—	5.0	mA
$T_C = 25^\circ\text{C}$		—	10	
$T_C = -65^\circ\text{C}$		—		

1. Ratings apply for zero or negative gate voltage but positive gate voltage shall not be applied concurrently with a negative potential on the anode. When checking forward or reverse blocking capability, thyristor devices should not be tested with a constant current source in a manner that the voltage applied exceeds the rated blocking voltage.
2. Forward current applied for 1.0 ms maximum duration, duty cycle $\leq 1.0\%$.
3. R_{GK} current is not included in measurement.

FIGURE 1 – SURGE RATINGS

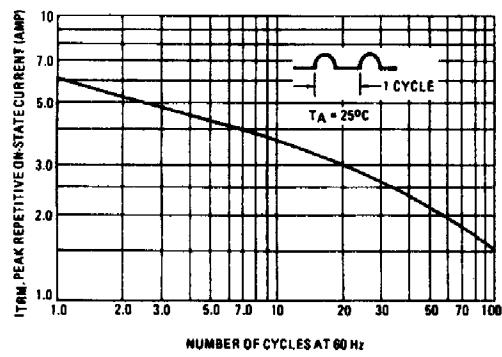


FIGURE 2 – POWER DISSIPATION

